

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	((semiconductor and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$5) or ("ALD"))) with (silicon or ("Si"))) with (ungsten or ("W")))) and (repeat\$5 or repet\$5)) and plasma).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 06:20
L2	0	((semiconductor and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$5) or ("ALD"))) with (silicon or ("Si"))) with (ungsten or ("W")))) and (repeat\$5 or repet\$5)) and plasma).clm.	US-PGPUB	OR	ON	2005/12/21 06:20
L3	0	((semiconductor and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$5) or ("ALD"))) with (silicon or ("Si"))) with (tungsten or ("W")))) and (repeat\$5 or repet\$5)) and plasma).clm.	US-PGPUB	OR	ON	2005/12/21 06:20
L4	0	((semiconductor and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$5) or ("ALD"))) with (silicon or ("Si"))) with (tungsten or ("W")))) and (repeat\$5 or repet\$5)) and plasma).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 06:21
L5	5	((semiconductor and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) and ((atomic adj layer deposit\$5) or ("ALD"))) and (silicon or ("Si"))) and (tungsten or ("W")))) and (repeat\$5 or repet\$5)) and plasma).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 06:22

L6	1	((semiconductor and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) and ((atomic adj layer deposit\$5) or ("ALD"))) and (silicon or ("Si"))) and (tungsten or ("W"))) and (repeat\$5 or repet\$5)) and plasma).clm.	US-PGPUB	OR	ON	2005/12/21 06:21
S1	1	("20020151110").PN.	US-PGPUB; USOCR	OR	OFF	2005/01/10 09:32
S2	1	(tantalum adj nitride) with (ligand adj bond\$5) with (free near5 ((hydrogen or ("H.sub.2"))) adj radical))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 09:13
S3	1078	semiconductor and ((insulat\$ or dielectric or oxide) adj (layer or film)) and (hole or aperture or via or trench or open\$4) and ((atomic adj layer adj deposit\$6) or ("ALD"))) and (repeat\$8 or times) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 11:33
S4	745	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) same (hole or aperture or via or trench or open\$4)) and ((atomic adj layer adj deposit\$6) or ("ALD"))) and (repeat\$8 or times) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 08:33
S5	595	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) with (hole or aperture or via or trench or open\$4)) and ((atomic adj layer adj deposit\$6) or ("ALD"))) and (repeat\$8 or times) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 11:32
S6	457	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) with (hole or aperture or via or trench or open\$4)) and ((atomic adj layer adj deposit\$6) or ("ALD"))) and (repeat\$8 or times) and (barrier or (diffus\$6 adj prevent\$6)) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 11:33

S7	552	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) same (hole or aperture or via or trench or open\$4)) and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and (barrier or (diffus\$6 adj prevent\$6)) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 11:33
S8	752	semiconductor and ((insulat\$ or dielectric or oxide) adj (layer or film)) and (hole or aperture or via or trench or open\$4) and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and (barrier or (diffus\$6 adj prevent\$6)) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 11:33
S9	222	semiconductor and (insulat\$ adj layer) and hole and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and (barrier) and @ad<="20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 12:00
S10	22254	lim.inv.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 11:58
S11	173	lim.inv. and bio	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 12:04
S12	3	lim.inv. and bi and (atomic adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 12:05
S13	239	lim.inv. and bi and o	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 12:05
S14	1	(lim.inv. and bi and o) and (atomic adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 12:05

S15	738	(438/652).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:56
S16	232	438/652.ccls. and barrier and ((atomic adj layer deposit\$6) or ("ALD"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 09:08
S17	1	("20040115929").PN.	US-PGPUB; USOCR	OR	OFF	2004/10/18 09:02
S18	2172	(438/586).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:11
S19	276	(438/658).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:11
S20	953	(438/653).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:11
S21	1261	(438/643).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:11
S22	652	(438/683).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/18 10:11
S23	2089	438/652,653,658,643,683,586. ccls. and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and @ad<"20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 10:12

S24	1876	438/652,653,658,643,683,586. ccls. and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and @ad<"20031210"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 10:14
S25	378	(438/652,653,658,643,683,586. ccls. and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and @ad<"20031210") and repe\$9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 13:41
S26	3	((("6482733") or ("6391785") or ("6139700")).PN.	USPAT; USOCR	OR	OFF	2004/10/19 08:13
S27	5	((("6383924") or ("5811868") or ("4751562") or ("5805421") or ("6440637")).PN.	USPAT; USOCR	OR	OFF	2004/10/20 08:48
S28	8	"5746826".URPN.	USPAT	OR	ON	2004/09/01 11:55
S29	3	("5013683" "5134091" "5416331").PN.	USPAT	OR	ON	2004/09/01 11:55
S30	0	lim.inv. and bio and ((atomic adj layer adj deposit\$6) or ("ALD"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 12:01
S31	0	lim.inv. and bio and (atomic adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/01 12:02
S32	16	optoelectronic with ablation with laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/19 10:33
S33	9	("4058430" "5288379" "5338423" "5780908" "5858184" "5873942" "5911857" "5973402" "5998870").PN.	USPAT	OR	ON	2004/10/19 12:49
S34	26	"6139700".URPN.	USPAT	OR	ON	2004/10/19 12:55
S35	15	("4058430" "4413022" "4747367" "4761269" "5711811" "5879459" "5904565" "5916365" "6077775" "6083818" "6100184" "6184128" "6200893" "6203613" "6270572").PN.	USPAT	OR	ON	2004/10/19 13:02

S36	14	("4058430" "4413022" "4747367" "4761269" "5071670" "5306666" "5711811" "5769950" "5879459" "5904565" "5916365" "6077775" "6083818" "6380065").PN.	USPAT	OR	ON	2004/10/19 13:21
S37	2	((("6300679") or ("20040021211"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/10/19 13:51
S38	1	("20040115913").PN.	US-PGPUB; USOCR	OR	OFF	2005/01/10 10:20
S39	1	("20040115913").PN.	US-PGPUB; USOCR	OR	OFF	2005/01/10 10:29
S40	3	((("6482733") or ("6391785") or ("6139700"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/06/24 12:28
S41	0	(438/652,653,658,643,683,586. ccls. and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD"))) and repe\$9).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:01
S42	0	("438"/\$.ccls. and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD"))) and repe\$9).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 13:43
S43	0	("438"/\$.ccls. and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD"))) and repe\$9).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 13:44
S44	0	("257"/\$.ccls. and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD"))) and repe\$9).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 13:44
S45	201	(semiconductor and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD"))) and repe\$9).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 13:45
S46	100	(semiconductor and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD"))) and repe\$9).clm.	US-PGPUB	OR	ON	2005/12/20 13:45

S47	9	(semiconductor and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and ((tungsten adj nitride) or ("WN")) and repe\$9). clm.	US-PGPUB	OR	ON	2005/12/20 13:56
S48	1053	(semiconductor and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and ((tungsten adj nitride) or ("WN")) and repe\$9)	US-PGPUB	OR	ON	2005/12/20 13:56
S49	767	(semiconductor and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and ((tungsten adj nitride) or ("WN")) and repe\$9) and plasma	US-PGPUB	OR	ON	2005/12/20 13:57
S50	226	(semiconductor and (hole or open\$6 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$6) or ("ALD"))) and repe\$9) and plasma	US-PGPUB	OR	ON	2005/12/20 14:00
S51	0	(438/652,653,658,643,683,586. ccls. and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and repeat\$9).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:01
S52	0	("438"/\$.ccls. and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and repeat\$9).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:01
S53	322	("257"/\$.ccls. and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$5) or ("ALD"))) and (repeat\$5 or repet\$5)) and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:04
S54	274	("438"/\$.ccls. and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$5) or ("ALD"))) and (repeat\$5 or repet\$5)) and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:53

S55	412	(semiconductor and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$5) or ("ALD"))) and (repeat\$5 or repet\$5)) and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:06
S56	6	((semiconductor and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$5) or ("ALD"))) and (repeat\$5 or repet\$5)) and plasma).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:08
S57	1	((semiconductor and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$5) or ("ALD"))) and (repeat\$5 or repet\$5)) and plasma).clm.	US-PGPUB	OR	ON	2005/12/20 14:07
S58	76	("438"/\$.ccls. and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$5) or ("ALD"))) with (silicon or ("Si")) with (ungsten or ("W"))) and (repeat\$5 or repet\$5)) and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:54
S59	81	("257"/\$.ccls. and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$5) or ("ALD"))) with (silicon or ("Si")) with (ungsten or ("W"))) and (repeat\$5 or repet\$5)) and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/20 14:54
S60	103	(semiconductor and (hole or open\$3 or aperture or groove or trench or via) and barrier and (((tungsten adj nitride) or ("WN"))) with ((atomic adj layer deposit\$5) or ("ALD"))) with (silicon or ("Si")) with (ungsten or ("W"))) and (repeat\$5 or repet\$5)) and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/21 06:20